

**MMBTA56**

**PNP EPTAXIAL SILICON TRANSISTOR**

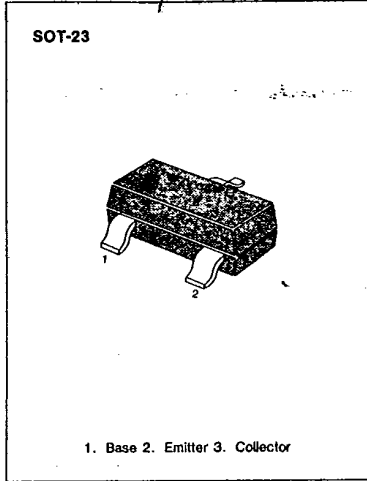
T-29-19

**DRIVER TRANSISTOR**

**ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-80	V
Collector-Emitter Voltage	V <sub>CE0</sub>	-80	V
Emitter-Base Voltage	V <sub>EB0</sub>	-4	V
Collector Current	I <sub>C</sub>	-500	mA
Collector Dissipation	P <sub>C</sub>	350	mW
Storage Temperature	T <sub>stg</sub>	150	°C
Thermal Resistance Junction to Ambient	R <sub>th(j-a)</sub>	357	°C/W

• Refer to MPSA55 for graphs

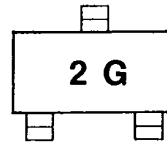


**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C)**

Characteristic	Symbol	Test Condition	Min	Max	Unit
*Collector-Emitter Breakdown Voltage	BV <sub>CE0</sub>	I <sub>C</sub> = -1mA, I <sub>B</sub> = 0	-80		V
Emitter-Base Breakdown Voltage	BV <sub>EB0</sub>	I <sub>E</sub> = -100μA, I <sub>C</sub> = 0	-4		V
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = -80V, I <sub>E</sub> = 0		-0.1	μA
Collector Cutoff Current	I <sub>CE0</sub>	V <sub>CE</sub> = -60V, I <sub>B</sub> = 0		-0.1	μA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = -1V, I <sub>C</sub> = -10mA	50		
		V <sub>CE</sub> = -1V, I <sub>C</sub> = -100mA	50		
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA		-0.25	V
Base-Emitter On Voltage	V <sub>BE(on)</sub>	V <sub>CE</sub> = -1V, I <sub>C</sub> = -100mA		-1.2	V
Current Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = -1V, I <sub>C</sub> = -100mA, f = 100MHz	50		MHz

\* Pulse Test: PW ≤ 300μs, Duty Cycle ≤ 2%

**Marking**



3

